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Technical Note

Protection Components

Step-up/down, High-efficiency Switching Regulators (Controller type)

Large Current External FET Controller Type Switching Regulators

BD8303MUV

No.09028EAT02

General Description

ROHM's highly-efficient step-up/down switching regulator BD8303MUV generates step-up/down output including 3.3 V / 5 V from 1 cell of lithium battery, 4 batteries, or 2 cells of Li batteries with just one inductor. This IC adopts an original step-up/down drive system and creates a higher efficient power supply than conventional Sepic-system or H-bridge system switching regulators.

Features

- 1)Highly-efficient step-up/down DC/DC converter to be constructed just with one inductor.
- 2) Supports a wide range of power supply voltage range (input voltage: 2.7 V 14.0 V)
 - 3) Supports high-current application with external Nch FET.
 - 4) Incorporates soft-start function.
 - 5) Incorporates timer latch system short protecting function.
 - 6) High heat radiation surface mounted package QFN16 pin, 3 mm × 3 mm

Application

General portable equipment like DVC, single-lens reflex cameras, portable DVDs, or mobile PCs

Absolute Maximum Ratings

| Parameter | Symbol | Rating | Unit |
|-------------------------------|----------------------------------|-------------|------|
| | VCC | 15 | V |
| | VREG | 7 | V |
| Maximum applied power voltage | Between BOOT 1, 2 and SW 1, 2 | 7 | V |
| | Between BOOT 1, 2 and GND | 20 V | |
| | SW1, 2 | 15 | V |
| Power dissipation | Pd | 620 | mW |
| Operating temperature range | Topr | -25 to +85 | °C |
| Storage temperature range | Tstg | -55 to +150 | °C |
| Junction temperature | Tjmax | +150 | °C |

When installed on a 70.0 mm \times 70.0 mm \times 1.6 mm glass epoxy board. The rating is reduced by 4.96 mW/°C at Ta = 25°C or more.

• Operating Conditions (Ta = 25°C)

| Parameter | Symbol | Standard | value | | Unit |
|-----------------------|--------|----------|-------|-----|------|
| Farameter | Symbol | MIN | TYP | MAX | Unit |
| Power supply voltage | VCC | 2.7 | - | 14 | V |
| Output voltage | VOUT | 1.8 | — | 12 | V |
| Oscillation frequency | fosc | 0.2 | 0.6 | 1.0 | MHz |

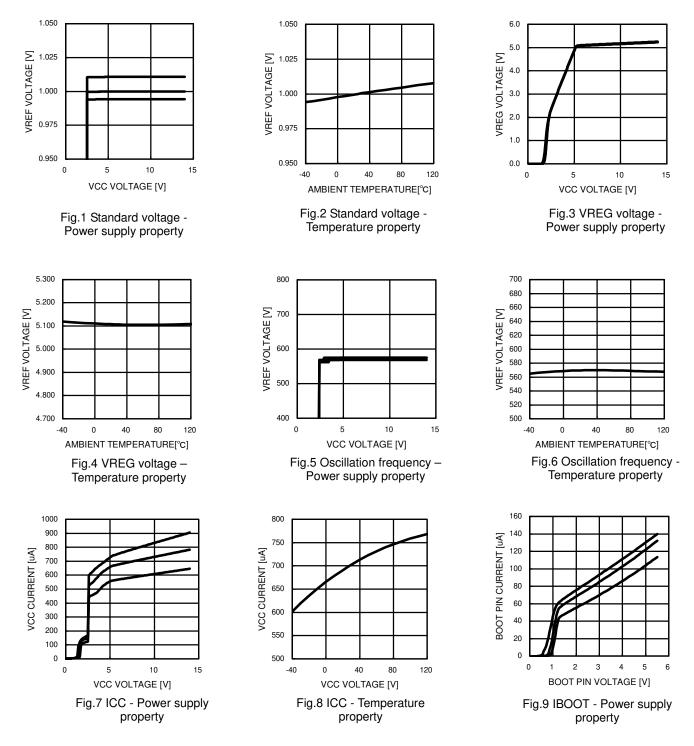
* These specifications are subject to change without advance notice for modifications and other reasons.

BD8303MUV

Electrical Characteristics (Unless otherwise specified, Ta = 25 °C, VCC = 7.4 V)

| | | - | Target Valu | e | | 0 |
|---|--|---------|-------------|---------|------|-----------------------|
| Parameter | Symbol | Minimum | Typical | Maximum | Unit | Conditions |
| [Low voltage input malfunction prev | enting circui | t] | | 1 | | |
| Detection threshold voltage | Vuv | - | 2.4 | 2.6 | V | VREG monitor |
| Hysteresis range | ΔVuvhy | 50 | 100 | 200 | mV | |
| [Oscillator] | - | | | | | |
| Oscillation frequency | fosc | 480 | 600 | 720 | kHz | Rτ=51kΩ |
| [Regulator] | | | | | | |
| Output voltage | VREG | 4.7 | 5.1 | 5.5 | V | |
| [Error AMP] | | | | | | |
| INV threshold voltage | VINV | 0.9875 | 1.00 | 1.0125 | V | |
| Input bias current | IINV | -50 | 0 | 50 | nA | Vcc=12.0V , IINV=6.0V |
| Soft-start time | Tss 2.4 4.0 5.6 msec RT=51kΩ rrent IEO 10 20 30 μA VINV=0.8V , VFB =1.5V | | | | | |
| Output source current | IEO | | | 30 | μA | |
| Output sink current | lei | 0.6 | 1.3 | 3 | mA | VINV=1.2V , VFB =1.5V |
| [PWM comparator] | | | | | | |
| SW1 Max Duty | Dmax1 | 85 | 90 | 95 | % | HG1 ON |
| SW2 Max Duty | uty Dmax1 85 90 95 % HG1 ON uty Dmax2 85 90 95 % LG2 ON | | LG2 ON | | | |
| SW2 Min Duty | Dmin2 | 5 | 10 | 15 | % | LG2 OFF |
| [Output] | | | | | | |
| HG1, 2 High side ON resistance | RonHp | - | 4 | 8 | Ω | |
| HG1, 2 Low side ON resistance | RonHn | - | 4 | 8 | Ω | |
| LG1, 2 High side ON resistance | RonLp | - | 4 | 8 | Ω | |
| LG1, 2 Low side ON resistance | RonLn | - | 4 | 8 | Ω | |
| HG1-LG1 dead time | Tdead1 | 50 | 100 | 200 | nsec | |
| HG2-LG2 dead time | Tdead2 | 50 | 100 | 200 | nsec | |
| [STB] | - | | | | | |
| STB pin Operation | VsтвH | 2.5 | - | VCC | V | |
| control voltage No-operation | VSTBL | -0.3 | - | 0.3 | V | |
| STB pin pull-down resistance | RSTB | 250 | 400 | 700 | kΩ | |
| [Circuit current] | - | | | | | 1 |
| Standby current VCC pin | Istb | - | - | 1 | μA | |
| Circuit current at operation VCC | lcc1 | - | 650 | 1000 | μA | VINV=1.2V |
| Circuit current at operation BOOT1,2 | lcc2 | - | 120 | 240 | μA | VINV=1.2V |

Reference Data



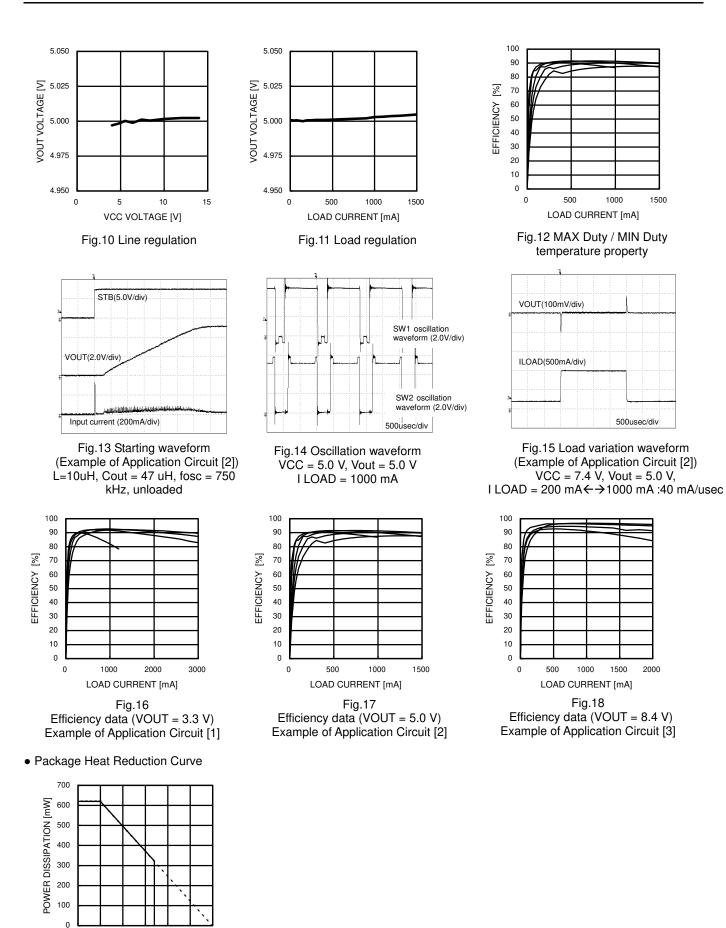


Fig.19 heat reduction curve (IC alone) When used at Ta = 25° C or more, it is reduced by 4.96 mW/°C.

AMBIENT TEMPERATURE[°C]

0 25 50 75 100 125 150

Description of Pins

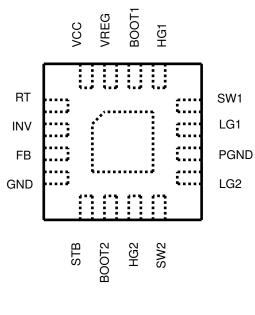


Fig. 20 Pin layout

| Pin No. | Pin Name | Function |
|---------|----------|---|
| 1 | RT | Oscillation frequency set terminal |
| 2 | INV | Error AMP input terminal |
| 3 | FB | Error AMP output terminal |
| 4 | GND | Ground terminal |
| 5 | STB | ON/OFF terminal |
| 6 | BOOT2 | Output side high-side driver input terminal |
| 7 | HG2 | Output side high-side FET gate drive terminal |
| 8 | SW2 | Output side coil connecting terminal |
| 9 | LG2 | Output side low-side FET gate drive terminal |
| 10 | PGND | Driver part ground terminal |
| 11 | LG1 | Input side low-side FET gate drive terminal |
| 12 | SW1 | Input side coil connecting terminal |
| 13 | HG1 | Input side high-side FET gate drive terminal |
| 14 | BOOT1 | Input side high-side driver input terminal |
| 15 | VREG | 5 V internal regulator output terminal |
| 16 | VCC | Power input terminal |

Block Diagram

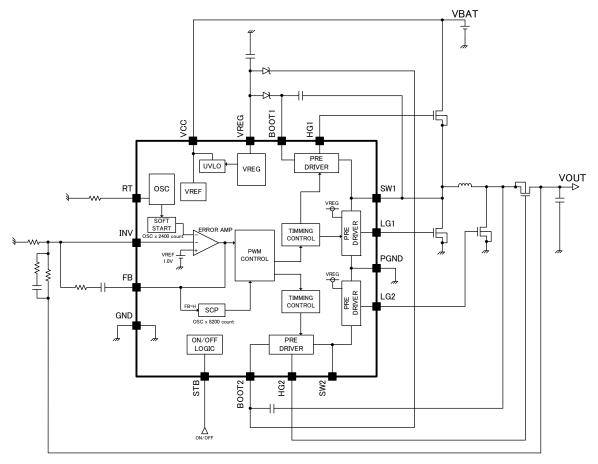


Fig. 21 Block diagram

Description of Blocks

1. VREF

This block generates ERROR AMP reference voltage. The reference voltage is 1.0 V.

2. VREG

5.0 V output voltage regulator. Used as power supply for IC internal circuit and BOOT pin supply. Follows power supply voltage when it is 5.0 V or below and also drops output voltage. For external oscillation preventive capacitor, 1.0 uF is recommended.

3. UVLO

Circuit for preventing low voltage malfunction

Prevents malfunction of the internal circuit at activation of the power supply voltage or at low power supply voltage. Monitors VREG pin voltage to turn off DC/DC converter output by changing output voltage of HG1, 2 and LG1, 2 pin to L-logic when VREG voltage is 2.4 V or below, and reset the timer latch of the internal SCP circuit and soft-start circuit.

4. SCP

Timer latch system short-circuit protection circuit

When the INV pin is the set 1.0 V or lower voltage, the internal SCP circuit starts counting.

The internal counter is in synch with OSC; the latch circuit activates after the counter counts about 8200 oscillations to turn off DC/DC converter output (about 13.6 msec when RT = 51 k Ω).

To reset the latch circuit, turn off the STB pin once. Then, turn it on again or turn on the power supply voltage again.

5. OSC

Oscillation circuit to change frequency by external resistance of the RT pin (1 pin). When RT = 51 k Ω , operation frequency is set at 600 kHz.

6. ERROR AMP

Error amplifier for detecting output signals and output PWM control signals The internal reference voltage is set at 1.0 V.

7. PWM COMP

Voltage-pulse width converter for controlling output voltage corresponding to input voltage Comparing the internal SLOPE waveform with the ERROR AMP output voltage, PWM COMP controls the pulse width and outputs to the driver.

Also controls Max Duty and Min Duty.

Max Duty and Min Duty are set at the primary side and the secondary side of the inductor respectively, which are as follows:

| Primary side (SW1) | HG1 Max Duty | : | About 90 %, |
|-----------------------|--------------|---|-------------|
| | HG1 Min Duty | : | 0 % |
| Secondary side (SW 2) | LG2 Max Duty | : | About 90 %, |
| | LG2 Min Duty | : | About 10 %, |

8. SOFT START

Circuit for preventing in-rush current at startup by bringing the output voltage of the DC/DC converter into a soft-start Soft-start time is in synch with the internal OSC, and the output voltage of the DC/DC converter reaches the set voltage after about 2400 oscillations (About 4 msec when RT = 51 k Ω).

9. Nch DRIVER

CMOS inverter circuit for driving external Nch FET. Dead time is provided for preventing feedthrough during switching of HG1 = L \rightarrow LG1 = H, HG2 = L \rightarrow LG2 = H and LG1 = L \rightarrow HG1 = H, LG2 = L \rightarrow HG2 = H.

The dead time is set at about 100 nsec in the internal circuit.

10. ON/OFF LOGIC

Voltage applied on STB pin (5 pin) to control ON/OFF of IC. Turned ON when a voltage of 2.5 V or higher is applied and turned OFF when the terminal is open or 0 V is applied.

Incorporates approximately 400 k Ω pull-down resistance.

• Example of Application Circuit

* Example of application circuit: VCC = 2.7 - 5.5V, Vout = 3.3V, Iout = 100 mA - 2000 mA

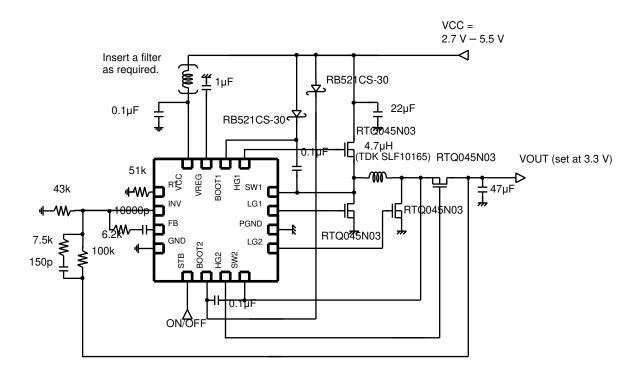


Fig. 22 Example of application circuit (1)

* Example of application circuit: VCC=2.7 - 14 V, Vout=5.0 V, Iout=100 mA - 1500 mA

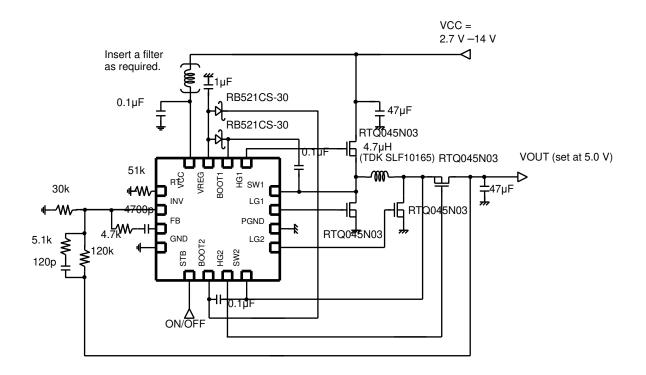
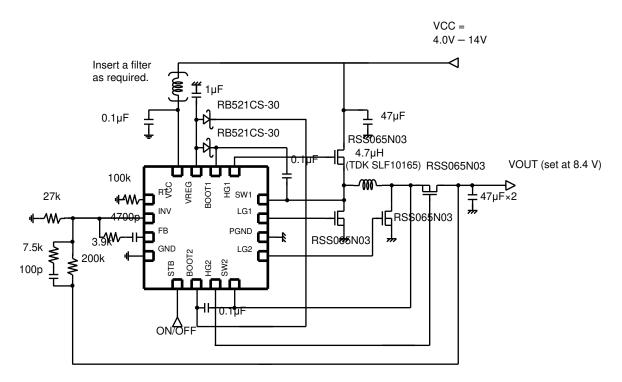
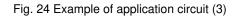


Fig. 23 Example of application circuit (2)

* Example of application circuit: VCC=4.0 - 14 V, Vout=8.4 V, Iout=100 mA - 1500 mA





* Example of application circuit:VCC=2.7 - 14 V, Vout=12 V, Iout=100 mA - 1500 mA

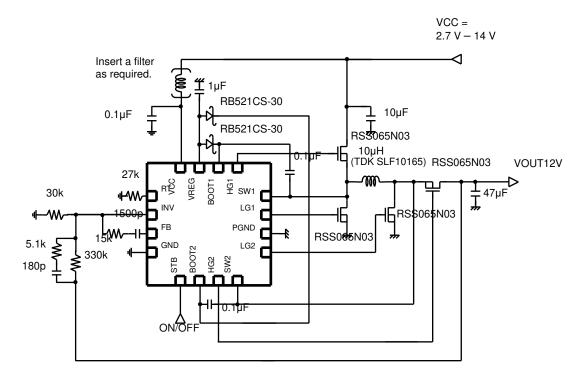


Fig. 25 Example of application circuit (4)

ΔIL

Fig. 26Ripple current

• Selection of parts for applications

(1) Output inductor

A shielded inductor that satisfies the current rating (current value, Ipeak as shown in the drawing below) and has a low DCR (direct current resistance component) is recommended.

(1)

Inductor values affect output ripple current greatly.

Ripple current can be reduced as the coil L value becomes larger and the switching frequency becomes higher as the equations shown below.

lpeak =lout ×(Vout/VIN) /
$$\eta$$
+ Δ IL/2 [A]

(η : Efficiency, Δ IL: Output ripple current, f: Switching frequency)

As a guide, output ripple current should be set at about 20 to 50% of the maximum output current.

* Current over the coil rating flowing in the coil brings the coil into magnetic saturation, which may lead to lower efficiency or output oscillation. Select an inductor with an adequate margin so that the peak current does not exceed the rated current of the coil.

(2) Output capacitor

A ceramic capacitor with low ESR is recommended for output in order to reduce output ripple. There must be an adequate margin between the maximum rating and output voltage of the capacitor, taking the DC bias property into consideration.

Output ripple voltage when ceramic capacitor is used is obtained by the following equation.

$$Vpp = \Delta IL \times \frac{1}{2\pi \times f \times Co} + \Delta IL \times R_{ESR} \quad [V] \quad \cdots \quad (5)$$
$$Vpp = \Delta IL \times \frac{1}{2\pi \times f \times Co} + \Delta IL \times R_{ESR} \quad [V] \quad \dots \quad (5)$$

Setting must be performed so that output ripple is within the allowable ripple voltage.

(3) External FET

An external FET which satisfies the following items and has small Ciss (input capacitance), Qg (total gate charge quantity) and ON resistance should be selected. There must be an adequate margin between the turn OFF time of MOS and the dead time to prevent through-current.

Drain-source voltage rating: (Output voltage + BodyDiode Vf of MOS or higher) Gate-source voltage rating: 7.0 V or higher Drain-source current rating: IPEAK of Output inductor paragraph or higher

BD8303MUV

(5) BOOT-SW capacitor

The capacitor between BOOT and SW should be designed so that the gate drive voltage will not be below Vgs necessary for the FET to use, taking circuit current input to the BOOT pin into consideration. There must be an adequate margin between the maximum rating and gate drive voltage.

| Gate drive voltage | |
|--|-----|
| = (VREG voltage) - (Vf of Di) - (Voltage drop by BOOT pin consumption) [V] | (6) |
| Voltage drop by BOOT pin consumption | |
| = (lboot × (1 / fosc) + Qg of external FET) / Cboot [V] | (7) |

(6) REG-BOOT diode

A Schottky diode which satisfies the following items and has less forward pressure drop (Vf) should be selected.

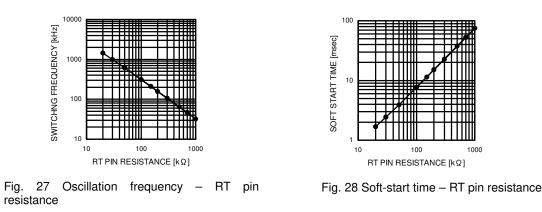
Average rectified current: There must be an adequate margin against the current consumed by MOSFET switching. DC inverse voltage: Input voltage or higher

(3) Setting of oscillation frequency

Oscillation frequency can be set using a resistance value connected to the RT pin (1 pin). Oscillation frequency is set at 600 kHz when RT = 51 k Ω , and frequency is inversely proportional to RT value. See Fig. 27 for the relationship between RT and frequency.

Soft-start time changes along with oscillation frequency.

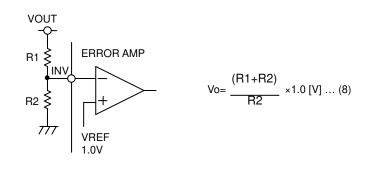
See Fig. 28 for the relationship between RT and soft-start time.

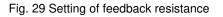


* Note that the above example of frequency setting is just a design target value, and may differ from the actual equipment.

(4) Output voltage setting

The internal reference voltage of the ERROR AMP is 1.0 V. Output voltage should be obtained by referring to Equation (8) of Fig. 29.





(9) Determination of external phase compensation

Condition for stable application

The condition for feedback system stability under negative feedback is as follows:

- Phase delay is 135 °or less when gain is 1 (0 dB) (Phase margin is 45° or higher)

Since DC/DC converter application is sampled according to the switching frequency, the GBW of the whole system (frequency at which gain is 0 dB) must be set to be equal to or lower than 1/5 of the switching frequency.

In summary, target property of applications is as follows:

- Phase delay must be 135° or lower when gain is 1 (0 dB) (Phase margin is 45° or higher).
- The GBW at that time (frequency when gain is 0 dB) must be equal to or lower than 1/5 of the switching frequency.

For this reason, switching frequency must be increased to improve responsiveness.

One of the points to secure stability by phase compensation is to cancel secondary phase delay (-180°) generated by LC resonance by the secondary phase lead (i.e. put two phase leads).

Since GBW is determined by the phase compensation capacitor attached to the error amplifier, when it is necessary to reduce GBW, the capacitor should be made larger. -20dB/decade

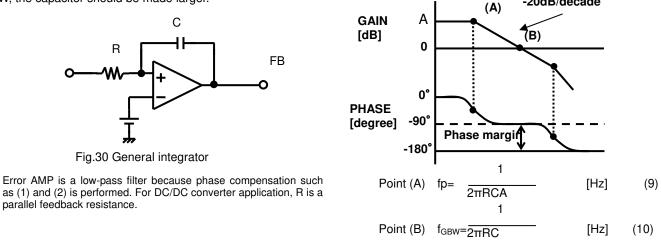


Fig.31 Frequency property of integrator

Phase compensation when output capacitor with low ESR such as ceramic capacitor is used is as follows:

When output capacitor with low ESR (several tens of $m\Omega$) is used for output, secondary phase lead (two phase leads) must be put to cancel secondary phase lead caused by LC.

One of the examples of phase compensation methods is as follows:

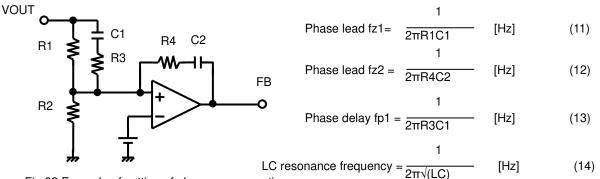


Fig.32 Example of setting of phase compensation

For setting of phase-lead frequency, both of them should be put near LC resonance frequency. When GBW frequency becomes too high due to the secondary phase lead, it may get stabilized by putting the primary phase delay in a frequency slightly higher than the LC resonance frequency to compensate it.

• Example of Board Layout

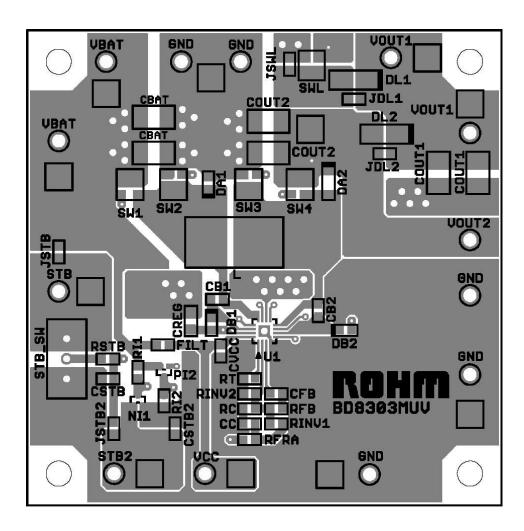
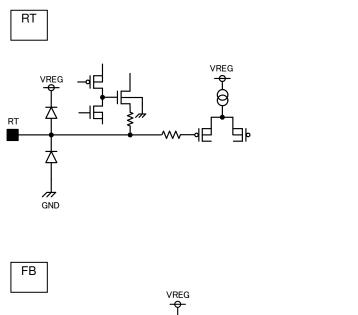
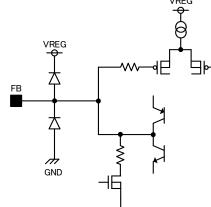
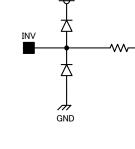


Fig.33 Example of Board Layout

• I/O Equivalence Circuit







VREG

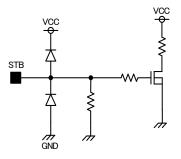
VREG

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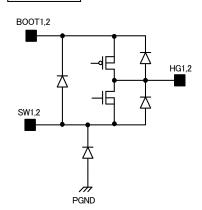
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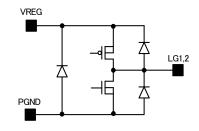
INV











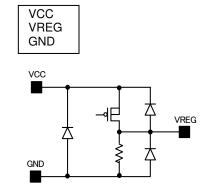


Fig.34 I/O equivalence circuit

• Precautions for Use

1) Absolute Maximum Rating

We dedicate much attention to the quality control of these products, however the possibility of deterioration or destruction exists if the impressed voltage, operating temperature range, etc., exceed the absolute maximum ratings. In addition, it is impossible to predict all destructive situations such as short-circuit modes, open circuit modes, etc. If a special mode exceeding the absolute maximum rating is expected, please review matters and provide physical safety means such as fuses, etc.

2) GND Potential

Keep the potential of the GND pin below the minimum potential at all times.

3) Thermal Design

Work out the thermal design with sufficient margin taking power dissipation (Pd) in the actual operation condition into account.

4) Short Circuit between Pins and Incorrect Mounting

Attention to IC direction or displacement is required when installing the IC on a PCB. If the IC is installed in the wrong way, it may break. Also, the threat of destruction from short-circuits exists if foreign matter invades between outputs or the output and GND of the power supply.

5) Operation under Strong Electromagnetic Field

Be careful of possible malfunctions under strong electromagnetic fields.

6) Common Impedance

When providing a power supply and GND wirings, show sufficient consideration for lowering common impedance and reducing ripple (i.e., using thick short wiring, cutting ripple down by LC, etc.) as much as you can.

7) Thermal Protection Circuit (TSD Circuit)

This IC contains a thermal protection circuit (TSD circuit). The TSD circuit serves to shut off the IC from thermal runaway and does not aim to protect or assure operation of the IC itself. Therefore, do not use the TSD circuit for continuous use or operation after the circuit has tripped.

8) Rush Current at the Time of Power Activation

Be careful of the power supply coupling capacity and the width of the power supply and GND pattern wiring and routing since rush current flows instantaneously at the time of power activation in the case of CMOS IC or ICs with multiple power supplies.

9) IC Terminal Input

This is a monolithic IC and has P+ isolation and a P substrate for element isolation between each element. P-N junctions are formed and various parasitic elements are configured using these P layers and N layers of the individual elements.

For example, if a resistor and transistor are connected to a terminal as shown on Fig.-8:

O The P-N junction operates as a parasitic diode when GND > (Terminal A) in the case of a resistor or when GND > (Pin B) in the case of a transistor (NPN)

O Also, a parasitic NPN transistor operates using the N layer of another element adjacent to the previous diode in the case of a transistor (NPN) when GND > (Pin B).

The parasitic element consequently rises under the potential relationship because of the IC's structure. The parasitic element pulls interference that could cause malfunctions or destruction out of the circuit. Therefore, use caution to avoid the operation of parasitic elements caused by applying voltage to an input terminal lower than the GND (P board), etc.

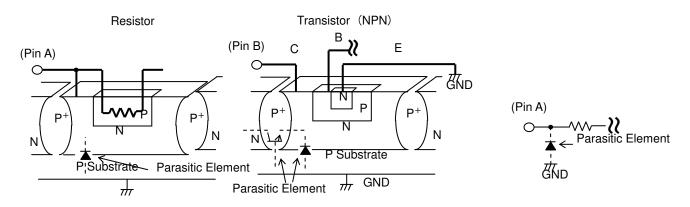
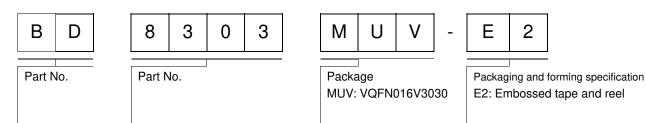


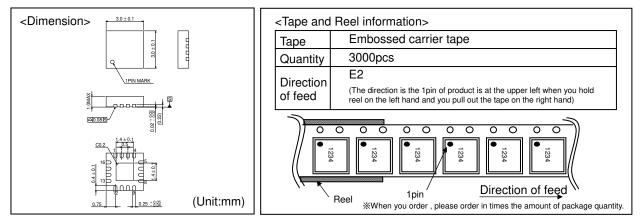
Fig.35 Example of simple structure of Bipolar IC

BD8303MUV

Ordering part number



VQFN016V3030



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